Hall IC Series / Hall IC(Latch type)



BU52001GUL, BU52011HFV, BU52021HFV, BU52015GUL, BU52025G, BU52051NVX, BD7411G

Description

The bipolar Hall ICs are magnetic switches that can operate both S-and N-pole, upon which the output goes from Hi to Low. In addition to regular single-output Hall ICs, We offers a line up of dual-output units with a reverse output terminal (active High).

Features

- 1) Bipolar detection
- 2) Micropower operation (small current using intermittent operation method)(BD7411G is excluded.)
- 3) Ultra-compact CSP4 package (BU52001GUL,BU52015GUL)
- 4) Ultra-Small outline package HVSOF5 (BU52011HFV,BU52021HFV)
- 5) Ultra-Small outline package SSON004X1216 (BU52051NVXV)
- 6) Small outline package (BU52025G,BD7411G)
- 7) Line up of supply voltage
 - For 1.8V Power supply voltage (BU52011HFV,BU52015GUL,BU52051NVX)
 - For 3.0V Power supply voltage (BU52001GUL)
 - For 3.3V Power supply voltage (BU52021HFV,BU52025G)
 - For 5.0V Power supply voltage (BD7411G)
- 8) Dual output type (BU52015GUL)
- 9) High ESD resistance 8kV(HBM)

Applications

Product Lineup

Mobile phones, notebook computers, digital video camera, digital still camera, white goods etc.

Product name	Supply voltage (V)	Operate point (mT)	Hysteresis (mT)	Period (ms)	Supply current (AVG) (A)	Output type	Package
BU52001GUL	2.40~3.30	+/-3.7 💥	0.8	50	8.0 μ	CMOS	VCSP50L1
BU52015GUL	1.65~3.30	+/-3.0 💥	0.9	50	5.0 μ	CMOS	VCSP50L1
BU52051NVX	1.65~3.30	+/-3.0 💥	0.9	50	5.0 μ	CMOS	SSON004X1216
BU52011HFV	1.65~3.30	+/-3.0 💥	0.9	50	5.0 μ	CMOS	HVSOF5
BU52021HFV	2.40~3.60	+/-3.7 💥	0.8	50	8.0 μ	CMOS	HVSOF5
BU52025G	2.40~3.60	+/-3.7 💥	0.8	50	8.0 μ	CMOS	SSOP5
BD7411G	4.50~5.50	+/-3.4 💥	0.4	-	2.0m	CMOS	SSOP5

%Plus is expressed on the S-pole; minus on the N-pole

Absolute Maximum Ratings

BU52001GUL (Ta=25°C)

PARAMETERS	SYMBOL	LIMIT	UNIT
Power Supply Voltage	V _{DD}	-0.1~+4.5 ^{**1}	V
Output Current	I _{OUT}	±1	mA
Power Dissipation	Pd	420 ^{**2}	mW
Operating Temperature Range	T _{opr}	-40~+85	°C
Storage Temperature Range	T _{stg}	-40~+125	°C

※1. Not to exceed Pd

%2. Reduced by 4.20mW for each increase in Ta of 1°C over 25°C (mounted on 50mm × 58mm Glass-epoxy PCB)

BU52051NVX (Ta=25°C)

PARAMETERS	SYMBOL	LIMIT	UNIT
Power Supply Voltage	V _{DD}	-0.1~+4.5 ^{**5}	V
Output Current	I _{OUT}	±0.5	mA
Power Dissipation	Pd	2049 ^{%6}	mW
Operating Temperature Range	T _{opr}	-40~+85	°C
Storage Temperature Range	T _{stg}	-40~+125	°C

※5. Not to exceed Pd

%6. Reduced by 20.49mW for each increase in Ta of 1°C over 25°C (mounted on 70mm × 70 mm × 1.6mm Glass-epoxy PCB)

BU52021NVX (Ta=25°C)

PARAMETERS	SYMBOL	LIMIT	UNIT
Power Supply Voltage	V _{DD}	-0.1~+4.5 ^{%9}	V
Output Current	I _{OUT}	±1	mA
Power Dissipation	Pd	536 ^{×10}	mW
Operating Temperature Range	T _{opr}	-40~+85	°C
XSto Nget Temperature Range	T _{stg}	-40~+125	°C

** 10. Reduced by5.36mW for each increase in Ta of 1°C over 25°C (mounted on 70mm × 70 mm × 1.6mm Glass-epoxy PCB)

BD7411G (Ta=25°C)

PARAMETERS	SYMBOL	LIMIT	UNIT
Power Supply Voltage	V _{DD}	-0.3~+7.0 ^{**13}	V
Output Current	I _{OUT}	±1	mA
Power Dissipation	Pd	540 ^{×14}	mW
Operating Temperature Range	T _{opr}	-40~+85	ő
Storage Temperature Range	T _{stg}	-55~+150	°C

X13. Not to exceed Pd

%14. Reduced by 5.40mW for each increase in Ta of 1°C over 25°C (mounted on 70mm \times 70 mm \times 1.6mm Glass-epoxy PCB)

BU52015GUL (Ta=25°C)

PARAMETERS	SYMBOL	LIMIT	UNIT
Power Supply Voltage	V_{DD}	-0.1~+4.5 ^{**3}	V
Output Current	I _{OUT}	±0.5	mA
Power Dissipation	Pd	420 ^{%4}	mW
Operating Temperature Range	T _{opr}	-40~+85	°C
Storage Temperature Range	T _{stg}	-40~+125	°C

3. Not to exceed Pd

※4. Reduced by 4.20mW for each increase in Ta of 1°C over 25°C (mounted on 50mm × 58mm Glass-epoxy PCB)

BU52011HFV (Ta=25°C)

PARAMETERS	SYMBOL	LIMIT	UNIT
Power Supply Voltage	V _{DD}	-0.1~+4.5 ^{**7}	V
Output Current	I _{OUT}	±0.5	mA
Power Dissipation	Pd	536 ^{%8}	mW
Operating Temperature Range	T _{opr}	-40~+85	°C
Storage Temperature Range	T _{stg}	-40~+125	°C

%7. Not to exceed Pd

%8. Reduced by 5.36mW for each increase in Ta of 1°C over 25°C (mounted on 70mm × 70 mm × 1.6mm Glass-epoxy PCB) BU52025G (Ta=25°C)

PARAMETERS	SYMBOL	LIMIT	UNIT
Power Supply Voltage	V _{DD}	-0.1~+4.5 [*]	V
Output Current	I _{OUT}	±1	mA
Power Dissipation	Pd	540 ^{%12}	mW
Operating Temperature Range	T _{opr}	-40~+85	°C
Storage Temperature Range	T _{stg}	-40~+125	°C

※11. Not to exceed Pd

%12. Reduced by 5.40mW for each increase in Ta of 1°C over 25°C (mounted on 70mm × 70 mm × 1.6mm Glass-epoxy PCB)

Magnetic, Electrical Characteristics

		LIMIT					
PARAMETERS	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS	
Power Supply Voltage	V _{DD}	2.4	3.0	3.3	V		
	B _{opS}	-	3.7	5.5	-		
Operate Point	BopN	-5.5	-3.7	-	mT		
	B _{rpS}	0.8	2.9	-	-		
Release Point	B _{rpN}	-	-2.9	-0.8	mT		
L hvetere eie	B _{hysS}	-	0.8	-	T		
Hysteresis	B _{hysN}	-	0.8	-	mT		
Period	T _p	-	50	100	ms		
Output High Voltage	V _{он}	V _{DD} -0.4	-	-	V	B _{rpN} <b<b<sub>rpS</b<b<sub>	
Output Low Voltage	V _{OL}	-	-	0.4	V	B <b<sub>opN,B_{opS}<b< td=""></b<></b<sub>	
Supply Current	I _{DD(AVG)}	-	8	12	μA	Average	
Supply Current During Startup Time	I _{DD(EN)}	-	4.7	-	mA	During Startup Time Value	
Supply Current During Standby Time	I _{DD(DIS)}	-	3.8	-	μA	During Standby Time Value	

BU52001GUL (Unless otherwise specified, V_{DD} =3.0V, Ta=25°C)

%15 B = Magnetic flux density

1mT=10Gauss

Positive ("+") polarity flux is defined as the magnetic flux from south pole which is direct toward to the branded face of the sensor.

After applying power supply, it takes one cycle of period (T_P) to become definite output. Radiation hardiness is not designed.

BU52015GUL (Unless otherwise specified, V_{DD} =1.80V, Ta=25°C)

	LI		LIMIT				
PARAMETERS	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS	
Power Supply Voltage	V _{DD}	1.65	1.80	3.30	V		
On anota Deint	B _{opS}	-	3.0	5.0	T		
Operate Point	BopN	-5.0	-3.0	-	mT		
	B _{rpS}	0.6	2.1	-	Ŧ		
Release Point	B _{rpN}	-	-2.1	-0.6	mT		
	B _{hysS}	-	0.9	-	T		
Hysteresis	B _{hysN}	-	0.9	-	mT		
Period	Tp	-	50	100	ms		
Output High Voltage	V _{он}	V _{DD} -0.2	-	-	V	OUT1: B_{rpN} <b<b<math>rpS %16 OUT2: B<b<math>opN, B_{opS}<b I_{OUT} = -0.5mA</b </b<math></b<b<math>	
Output Low Voltage	V _{OL}	-	-	0.2	V	OUT1: $B < B_{opN}$, $B_{opS} < B$ %16 OUT2: $B_{rpN} < B < B_{rpS}$ $I_{OUT} = +0.5mA$	
Supply Current 1	I _{DD1(AVG)}	-	5	8	μA	V _{DD} =1.8V, Average	
Supply Current During Startup Time 1	I _{DD1(EN)}	-	2.8	-	mA	V _{DD} =1.8V, During Startup Time Value	
Supply Current During Standby Time 1	I _{DD1(DIS)}	-	1.8	-	μA	V _{DD} =1.8V, During Standby Time Value	
Supply Current 2	I _{DD2(AVG)}	-	8	12	μA	V _{DD} =2.7V, Average	
Supply Current During Startup Time 2	I _{DD2(EN)}	-	4.5	-	mA	V _{DD} =2.7V, During Startup Time Value	
Supply Current During Standby Time 2	I _{DD2(DIS)}	-	4.0	-	μA	V _{DD} =2.7V, During Standby Time Value	

%16 B = Magnetic flux density

1mT=10Gauss

Positive ("+") polarity flux is defined as the magnetic flux from south pole which is direct toward to the branded face of the sensor.

After applying power supply, it takes one cycle of period (T_P) to become definite output. Radiation hardiness is not designed.

BU52051NVX , BU52011HFV (Unless otherwise specified, V_{DD} =1.80V, Ta=25°C)

	LIMIT					
PARAMETERS	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Power Supply Voltage	V _{DD}	1.65	1.80	3.30	V	
Operate Point	BopS	-	3.0	5.0	mT	
	B _{opN}	-5.0	-3.0	-		
Release Point	BrpS	0.6	2.1	-	mT	
Release Point	BrpN	-	-2.1	-0.6	1111	
Uniteracia	B _{hysS}	-	0.9	-	mT	
Hysteresis	B _{hysN}	-	0.9	-	m	
Period	Tp	-	50	100	ms	
Output High Voltage	Vон	V _{DD} -0.2	-	-	V	B _{rpN} <b<b<sub>rpS X17 I_{OUT} =-0.5mA</b<b<sub>
Output Low Voltage	V _{OL}	-	-	0.2	V	B <b<sub>opN, B_{opS}<b< td=""></b<></b<sub>
Supply Current 1	IDD1(AVG)	-	5	8	μA	V _{DD} =1.8V, Average
Supply Current During Startup Time 1	I _{DD1(EN)}	-	2.8	-	mA	V _{DD} =1.8V, During Startup Time Value
Supply Current During Standby Time 1	I _{DD1(DIS)}	-	1.8	-	μA	V _{DD} =1.8V, During Standby Time Value
Supply Current 2	I _{DD2(AVG)}	-	8	12	μA	V _{DD} =2.7V, Average
Supply Current During Startup Time 2	I _{DD2(EN)}	-	4.5	-	mA	V _{DD} =2.7V, During Startup Time Value
Supply Current During Standby Time 2	I _{DD2(DIS)}	-	4.0	-	μA	V _{DD} =2.7V, During Standby Time Value

BU52021HFV,BU52025G (Unless otherwise specified, V_{DD}=3.0V, Ta=25°C)

5052021HF V,8052025G (01)		LIMIT			· · · · · - ·		
PARAMETERS	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS	
Power Supply Voltage	V _{DD}	2.4	3.0	3.6	V		
Operate Point	BopS	-	3.7	5.5	mT		
	BopN	-5.5	-3.7	-			
Release Point	B _{rpS}	0.8	2.9	-	mT		
Release Folini	B _{rpN}	-	-2.9	-0.8	1111		
Hustorosia	B _{hysS}	-	0.8	-			
Hysteresis	B _{hysN}	-	0.8	-	mT		
Period	Tp	-	50	100	ms		
Output High Voltage	V _{OH}	V _{DD} -0.4	-	-	V	B _{rpN} <b<b<sub>rpS</b<b<sub>	
Output Low Voltage	V _{OL}	-	-	0.4	V	B <b<sub>opN, B_{opS}<b %17<br="">I_{OUT} =+1.0mA</b<sub>	
Supply Current	I _{DD(AVG)}	-	8	12	μA	Average	
Supply Current During Startup Time	I _{DD(EN)}	-	4.7	-	mA	During Startup Time Value	
Supply Current During Standby Time	I _{DD(DIS)}	-	3.8	-	μA	During Standby Time Value	

※17 B = Magnetic flux density

1mT=10Gauss

Positive ("+") polarity flux is defined as the magnetic flux from south pole which is direct toward to the branded face of the sensor.

After applying power supply, it takes one cycle of period (T_P) to become definite output. Radiation hardiness is not designed.

BD7411G (Unless otherwise specified, V_{DD} =5.0V, Ta=25°C)

			LIMIT				
PARAMETERS	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS	
Power Supply Voltage	V _{DD}	4.5	5.0	5.5	V		
On anota Daint	B _{opS}	-	3.4	5.6	T		
Operate Point	B _{opN}	-5.6	-3.4	-	mT		
	B _{rpS}	1.5	3.0	-	Ŧ		
Release Point	B _{rpN}	-	-3.0	-1.5	mT		
	B _{hysS}	-	0.4	-			
Hysteresis	B _{hysN}	-	0.4	-	mT		
Output High Voltage	V _{он}	4.6	-	-	V	B _{rpN} <b<b<sub>rpS</b<b<sub>	
Output Low Voltage	V _{OL}	-	-	0.4	V	B <b<sub>opN, B_{opS}<b ※18<br="">I_{OUT} =+1.0mA</b<sub>	
Supply Current	I _{DD}	-	2	4	mA		

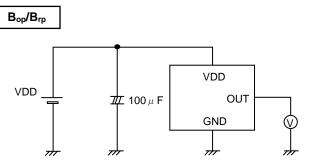
※18 B = Magnetic flux density

1mT=10Gauss

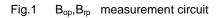
Positive ("+") polarity flux is defined as the magnetic flux from south pole which is direct toward to

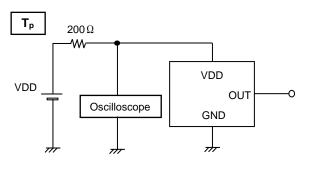
the branded face of the sensor.

Radiation hardiness is not designed.

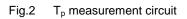


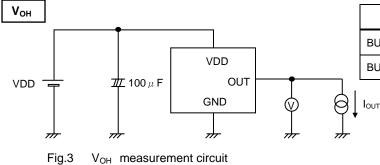
Bop and Brp are measured with applying the magnetic field from the outside.



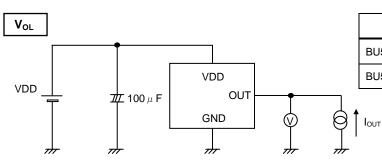


The period is monitored by Oscilloscope.





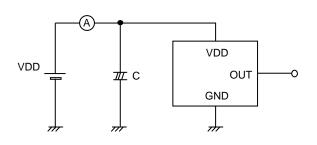
Product Name	I _{OUT}
BU52001GUL, BU52021HFV, BU52025G, BD7411G	1.0mA
BU52015GUL, BU52051NVX, BU52011HFV	0.5mA



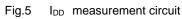
Product Name	I _{OUT}
BU52001GUL, BU52021HFV, BU52025G, BD7411G	1.0mA
BU52015GUL, BU52051NVX, BU52011HFV	0.5mA

I_{DD}

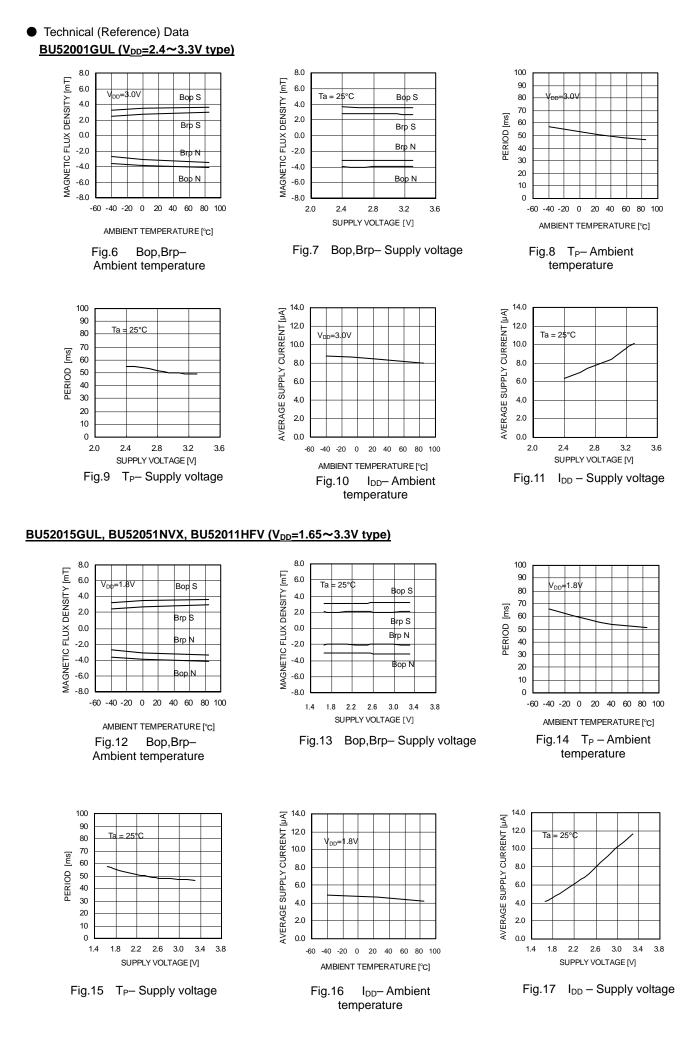
Fig.4



VoL measurement circuit



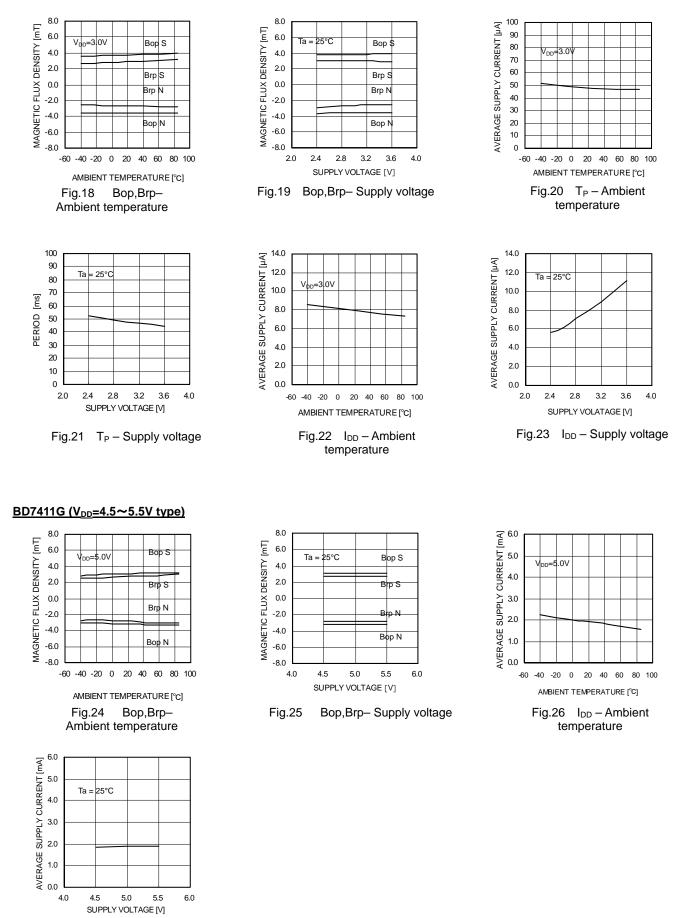
Product Name	С
BU52001GUL,BU52015GUL,BU52051NVX,	2200 μ F
BU52011HFV, BU52021HFV, BU52025G	2200 µ F
BD7411G	100 <i>µ</i> F



8/20

BU52021HFV, BU52025G (V_{DD}=2.4~3.6V type)

Fig.27 I_{DD} – Supply voltage



9/20

Block Diagram BU52001GUL

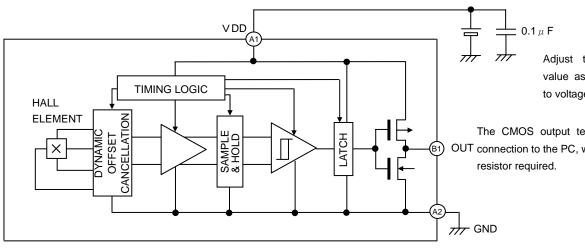
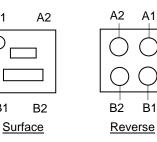


Fig.28

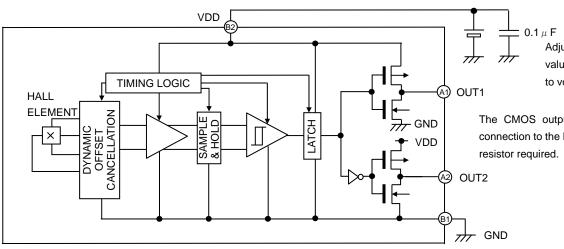
Adjust the bypass capacitor value as necessary, according to voltage noise conditions, etc.

The CMOS output terminals enable direct (B1) OUT connection to the PC, with no external pull-up

PIN No.	PIN NAME	FUNCTION	COMMENT	A1
A1	VDD	POWER SUPPLY		
A2	GND	GROUND		
B1	OUT	OUTPUT		
B2	N.C.		OPEN or Short to GND.	B1



BU52015GUL

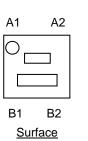


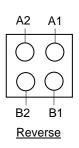
Adjust the bypass capacitor value as necessary, according to voltage noise conditions, etc.

The CMOS output terminals enable direct connection to the PC, with no external pull-up

Fig.29

PIN No.	PIN NAME	FUNCTION	COMMENT
A1	OUT1	Output pin (Active Low)	
A2	OUT2	Output pin (Active High)	
B1	GND	GROUND	
B2	VDD	Power Supply Voltage	





BU52051NVX

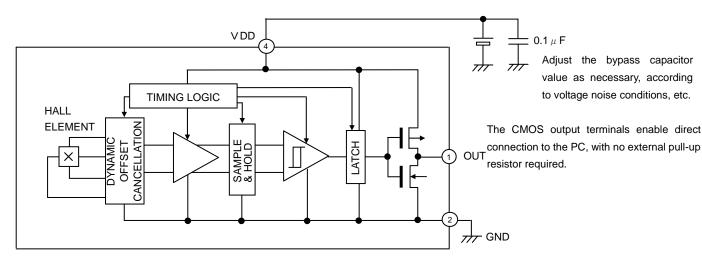


Fig.30

PIN No.	PIN NAME	FUNCTION	COMMENT
1	OUT	OUTPUT	
2	GND	GROUND	
3	N.C.		OPEN or Short to GND.
4	VDD	POWER SUPPLY	

BU52011HFV,BU52021HFV

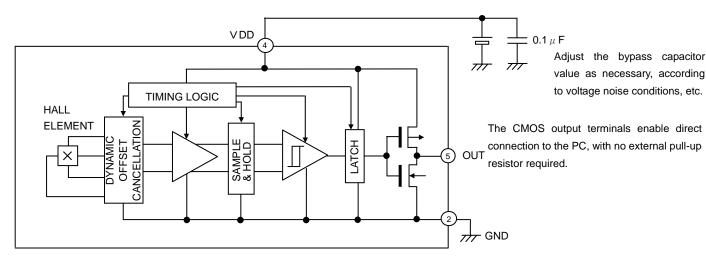
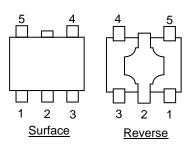


Fig.31

PIN No.	PIN NAME	FUNCTION	COMMENT
1	N.C.		OPEN or Short to GND.
2	GND	GROUND	
3	N.C.		OPEN or Short to GND.
4	VDD	POWER SUPPLY	
5	OUT	OUTPUT	



BU52025G

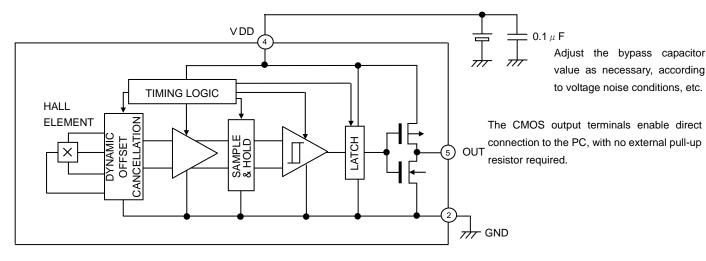
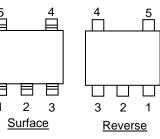
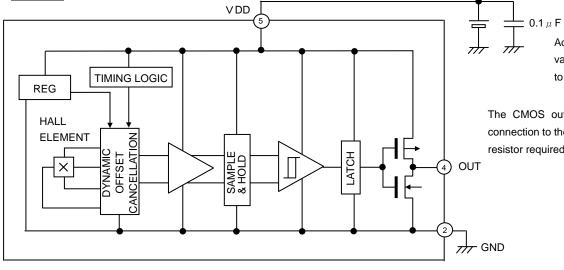


Fig.32

	PIN No.	PIN NAME	FUNCTION	COMMENT		
	1	N.C.		OPEN or Short to GND.	5	4
	2	GND	GROUND		[
	3	N.C.		OPEN or Short to GND.		
	4	VDD	POWER SUPPLY		EE	
ľ	5	OUT	OUTPUT		1 2 Surf	. 0



<u>BD7411G</u>

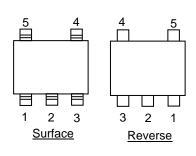


Adjust the bypass capacitor value as necessary, according to voltage noise conditions, etc.

The CMOS output terminals enable direct connection to the PC, with no external pull-up resistor required.

Fig.3	33
-------	----

PIN No.	PIN NAME	FUNCTION	COMMENT
1	N.C.		OPEN or Short to GND.
2	GND	GROUND	
3	N.C.		OPEN or Short to GND.
4	OUT	OUTPUT	
5	VDD	POWER SUPPLY	



Description of Operations

(Micropower Operation)

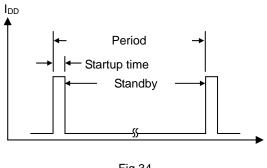


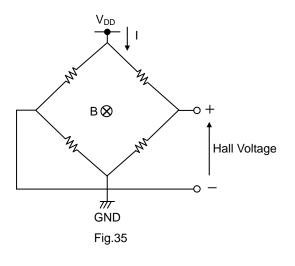
Fig.34

The bipolar detection Hall IC adopts an intermittent operation method to save energy. At startup, the Hall elements, amp, comparator and other detection circuits power ON and magnetic detection begins. During standby, the detection circuits power OFF, thereby reducing current consumption. The detection results are held while standby is active, and then output.

> Reference period: 50ms (MAX100ms) Reference startup time: 48μ s

%BD7411G don't adopts an intermittent operation method.

(Offset Cancelation)

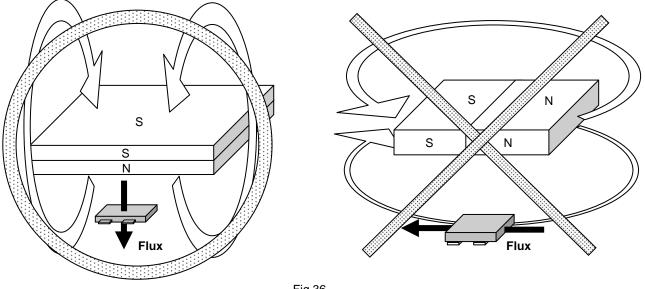


The Hall elements form an equivalent Wheatstone (resistor) bridge circuit. Offset voltage may be generated by a differential in this bridge resistance, or can arise from changes in resistance due to package or bonding stress. A dynamic offset cancellation circuit is employed to cancel this offset voltage.

When Hall elements are connected as shown in Fig. 35 and a magnetic field is applied perpendicular to the Hall elements, voltage is generated at the mid-point terminal of the bridge. This is known as Hall voltage.

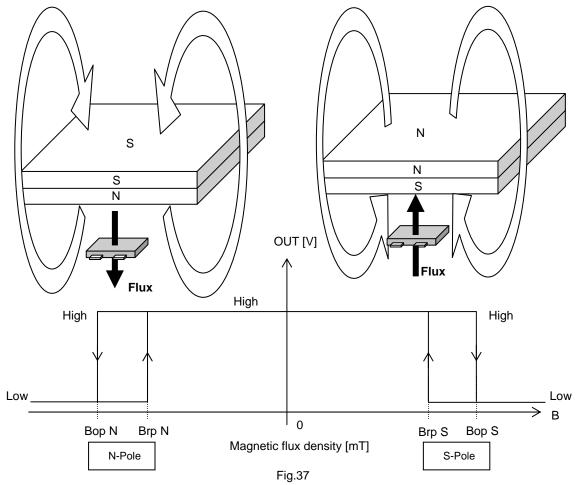
Dynamic cancellation switches the wiring (shown in the figure) to redirect the current flow to a 90° angle from its original path, and thereby cancels the Hall voltage.

The magnetic signal (only) is maintained in the sample/hold circuit during the offset cancellation process and then released.

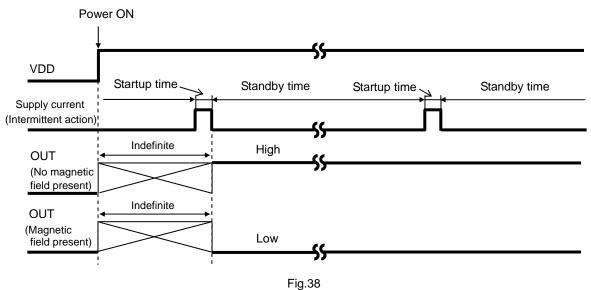




The Hall IC cannot detect magnetic fields that run horizontal to the package top layer. Be certain to configure the Hall IC so that the magnetic field is perpendicular to the top layer.



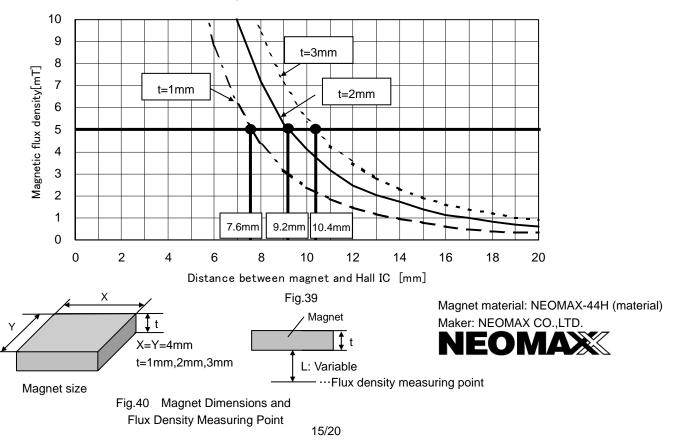
The bipolar detection Hall IC detects magnetic fields running perpendicular to the top surface of the package. There is an inverse relationship between magnetic flux density and the distance separating the magnet and the Hall IC: when distance increases magnetic density falls. When it drops below the operate point (Bop), output goes HIGH. When the magnet gets closer to the IC and magnetic density rises, to the operate point, the output switches LOW. In LOW output mode, the distance from the magnet to the IC increases again until the magnetic density falls to a point just below Bop, and output returns HIGH. (This point, where magnetic flux density restores HIGH output, is known as the release point, Brp.) This detection and adjustment mechanism is designed to prevent noise, oscillation and other erratic system operation.

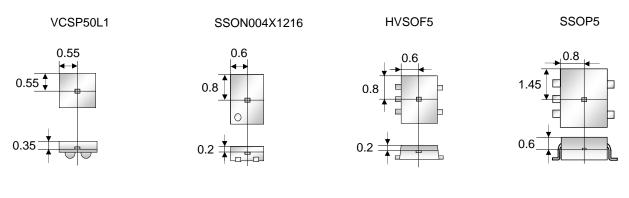


The bipolar detection Hall IC adopts an intermittent operation method in detecting the magnetic field during startup, as shown in Fig. 38. It outputs to the appropriate terminal based on the detection result and maintains the output condition during the standby period. The time from power ON until the end of the initial startup period is an indefinite interval, but it cannot exceed the maximum period, 100ms. To accommodate the system design, the Hall IC output read should be programmed within 100ms of power ON, but after the time allowed for the period ambient temperature and supply voltage. %BD7411G don't adopts an intermittent operation method.

Magnet Selection

Of the two representative varieties of permanent magnet, neodymium generally offers greater magnetic power per volume than ferrite, thereby enabling the highest degree of miniaturization, Thus, neodymium is best suited for small equipment applications. Fig. 39 shows the relation between the size (volume) of a neodymium magnet and magnetic flux density. The graph plots the correlation between the distance (L) from three versions of a 4mm X 4mm cross-section neodymium magnet (1mm, 2mm, and 3mm thick) and magnetic flux density. Fig. 40 shows Hall IC detection distance – a good guide for determining the proper size and detection distance of the magnet. Based on the BU52011HFV, BU52015GUL operating point max 5.0 mT, the minimum detection distance for the 1mm, 2mm and 3mm magnets would be 7.6mm, 9.22mm, and 10.4mm, respectively. To increase the magnet's detection distance, either increase its thickness or sectional area.

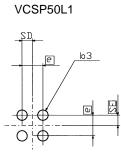




(UNIT : mm)

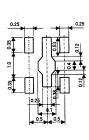
•Footprint dimensions (Optimize footprint dimensions to the board design and soldering condition)

SSON004X1216

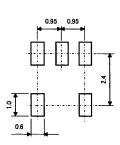


Symbol	Reference Value
e	0.50
b3	0.25
SD	0.25
SE	0.25





HVSOF5



SSOP5

(UNIT : mm)

Terminal Equivalent Circuit Diagram

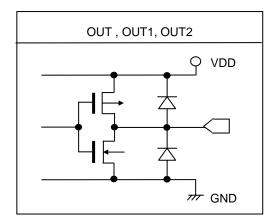


Fig.41

Because they are configured for CMOS (inverter) output, the output pins require no external resistance and allow direct connection to the PC. This, in turn, enables reduction of the current that would otherwise flow to the external resistor during magnetic field detection, and supports overall low current (micropower) operation.

Operation Notes

1) Absolute maximum ratings

Exceeding the absolute maximum ratings for supply voltage, operating conditions, etc. may result in damage to or destruction of the IC. Because the source (short mode or open mode) cannot be identified if the device is damaged in this way, it is important to take physical safety measures such as fusing when implementing any special mode that operates in excess of absolute rating limits.

2) GND voltage

Make sure that the GND terminal potential is maintained at the minimum in any operating state, and is always kept lower than the potential of all other pins.

3) Thermal design

Use a thermal design that allows for sufficient margin in light of the power dissipation (Pd) in actual operating conditions.

4) Pin shorts and mounting errors

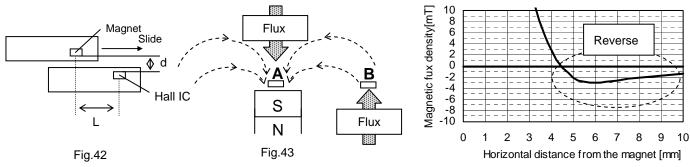
Use caution when positioning the IC for mounting on printed circuit boards. Mounting errors, such as improper positioning or orientation, may damage or destroy the device. The IC may also be damaged or destroyed if output pins are shorted together, or if shorts occur between the output pin and supply pin or GND.

5) Positioning components in proximity to the Hall IC and magnet

Positioning magnetic components in close proximity to the Hall IC or magnet may alter the magnetic field, and therefore the magnetic detection operation. Thus, placing magnetic components near the Hall IC and magnet should be avoided in the design if possible. However, where there is no alternative to employing such a design, be sure to thoroughly test and evaluate performance with the magnetic component(s) in place to verify normal operation before implementing the design.

6) Slide-by position sensing

Fig.42 depicts the slide-by configuration employed for position sensing. Note that when the gap (d) between the magnet and the Hall IC is narrowed, the reverse magnetic field generated by the magnet can cause the IC to malfunction. As seen in Fig.43, the magnetic field runs in opposite directions at Point A and Point B. Since the bipolar detection Hall IC can detect the S-pole at Point A and the N-pole at Point B, it can wind up switching output ON as the magnet slides by in the process of position detection. Fig. 44 plots magnetic flux density during the magnet slide-by. Although a reverse magnetic field was generated in the process, the magnetic flux density decreased compared with the center of the magnet. This demonstrates that slightly widening the gap (d) between the magnet and Hall IC reduces the reverse magnetic field and prevents malfunctions.



7) Operation in strong electromagnetic fields

Exercise extreme caution about using the device in the presence of a strong electromagnetic field, as such use may cause the IC to malfunction.

Fig.44

8) Common impedance

Make sure that the power supply and GND wiring limits common impedance to the extent possible by, for example, employing short, thick supply and ground lines. Also, take measures to minimize ripple such as using an inductor or capacitor.

9) GND wiring pattern

When both a small-signal GND and high-current GND are provided, single-point grounding at the reference point of the set PCB is recommended, in order to separate the small-signal and high-current patterns, and to ensure that voltage changes due to the wiring resistance and high current do not cause any voltage fluctuation in the small-signal GND. In the same way, care must also be taken to avoid wiring pattern fluctuations in the GND wiring pattern of external components.

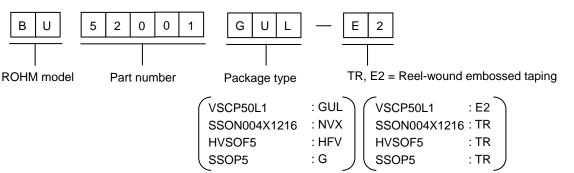
10) Exposure to strong light

Exposure to halogen lamps, UV and other strong light sources may cause the IC to malfunction. If the IC is subject to such exposure, provide a shield or take other measures to protect it from the light. In testing, exposure to white LED and fluorescent light sources was shown to have no significant effect on the IC.

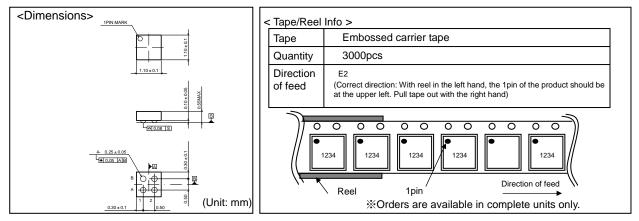
11) Power source design

Since the IC performs intermittent operation, it has peak current when it's ON. Please taking that into account and under examine adequate evaluations when designing the power source.

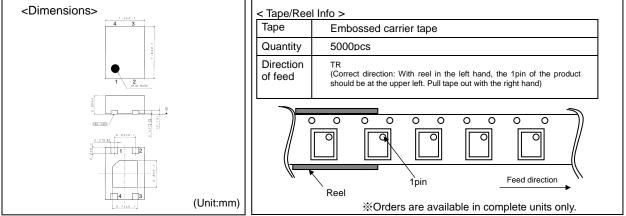
Product Designations (Selecting a model name when ordering)



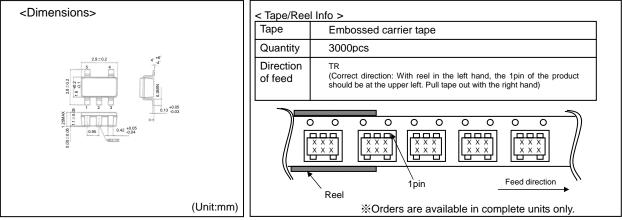
VCSP50L1



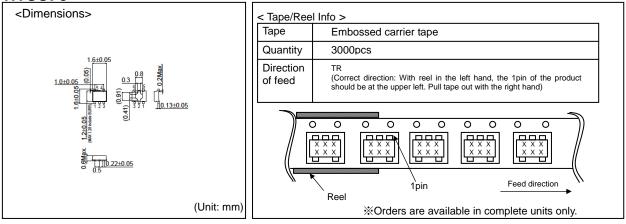
SSON004X1216



SSOP5



HVSOF5



- The contents described herein are correct as of June, 2008
- The contents described herein are subject to change without notice. For updates of the latest information, please contact and confirm with ROHM CO. LTD.
- Any part of this application note must not be duplicated or copied without our permission.
- Application circuit diagrams and circuit constants contained herein are shown as examples of standard use and operation. Please pay careful attention to the peripheral conditions when designing circuits and deciding upon circuit constants in the set.
- Any data, including, but not limited to application circuit diagrams and information, described herein are intended only as illustrations of such devices and not as the specifications for such devices. ROHM CO.,LTD. disclaims any warranty that any use of such devices shall be free from infringement of any third party's intellectual property rights or other proprietary rights, and further, assumes no liability of whatsoever nature in the event of any such infringement, or arising from or connected with or related to the use of such devices.
- Upon the sale of any such devices, other than for buyer's right to use such devices itself, resel or otherwise dispose of the same, implied right or license to practice or commercially exploit any intellectual property rights or other proprietary rights owned or controlled by ROHM CO., LTD. is granted to any such buyer.
- The products described herein utilize silicon as the main material.
 The products described herein are not designed to be X ray proof.

The products listed in this catalog are designed to be used with ordinary electronic equipment or devices (such as audio visual equipment, office-automation equipment, communications devices, electrical appliances and electronic toys).

Should you intend to use these products with equipment or devices which require an extremely high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), please be sure to consult with our sales representative in advance.

Contact us for further information about the products.





ROHM CO., LTD. 21, Saiin Mizosaki-cho, Ukyo-ku, Kyoto

615-8585. Japan TEL: +81-75-311-2121 FAX: +81-75-315-0172

URL http://www.rohm.com	Russia Seoul
Published by	Masan Dalian
LSI Business Promotion Dept.	Beijing Tianjin

San Diego Atlanta Boston Chicago Dallas FAX: +1-858-625-3670 FAX: +1-858-625-3670 FAX: +1-928-438-7164 FAX: +1-847-368-1008 FAX: +1-469-362-7973 FAX: +1-469-362-7973 FAX: +1-248-348-9942 FAX: +1-248-348-9942 FAX: +15-520-6570 TEL: +1-858-625-3630 TEL: +1-858-625-3630 TEL: +1-770-754-5972 TEL: +1-978-371-0382 TEL: +1-847-368-1006 TEL: +1-469-287-5366 TEL: +1-303-708-0908 TEL: +1-248-348-9920 Nashville TEL: +1-615-620-6700 FAX: +1-615-620-6702 TEL: +1-615-620-6700 TEL: +52-33-3123-2001 TEL: +49-2154-9210 TEL: +49-8161-48310 TEL: +49-711-72723710 TEL: +33-1-5697-3060 FAX: +1-615-620-6702 FAX: +52-33-3123-2002 FAX: +49-2154-921400 FAX: +49-8161-483120 FAX: +49-711-72723720 FAX: +33-1-5697-3080 Mashvine Mexico Düsseldorf Munich Stuttgart FAX: +43-1-908-235788 FAX: +45-3694-4789 FAX: +45-3694-4789 FAX: +36-1-4719339 FAX: +48-22-5757001 FAX: +795-937-8290 FAX: +82-2-8182-715 United Kingdom TEL: +44-1-908-306700 Denmark TEL: +45-3694-4739 TEL: +45-3694-4739 TEL: +34-9375-24320 TEL: +36-1-4719338 TEL: +48-22-5757213 TEL: +7-95-980-6755 TEL: +82-2-8182-700 Barcelona Hungary Poland TEL: +82-55-240-6234 FAX: +82-55-240-6236 TEL: +66-10-852-2400284 PAX: +86-411-8230-8537 TEL: +86-10-8525-2483 FAX: +86-10-8525-2489 TEL: +86-22-23029181 FAX: +86-22-23029183

Denver Detroit

France

Shanghai Shangha Hangzho Nanjing Ningbo Qingdao Suzhou Wuxi Wuxi Shenzhen Dongguan Fuzhou Guangzhou Huizhou Xiamen Zhuhai Hong Kong Taipei Kaohsiung Singapore Philippines Thailand Kuala Lumpur Penang Kyoto Yokohama

TEL: +86-21-6279-2727	FAX: +86-21-6247-2066
TEL: +86-571-87658072	FAX: +86-571-87658071
TEL: +86-25-8689-0015	FAX: +86-25-8689-0393
TEL: +86-574-87654201	FAX: +86-574-87654208
TEL: +86-532-5779-312	FAX:+86-532-5779-653
TEL: +86-512-6807-1300	FAX: +86-512-6807-2300
TEL: +86-510-82702693	FAX: +86-510-82702992
TEL: +86-755-8307-3008	FAX: +86-755-8307-3003
TEL: +86-769-8393-3320	FAX: +86-769-8398-4140
TEL: +86-591-8801-8698	FAX: +86-591-8801-8690
TEL: +86-20-8364-9796	FAX: +86-20-8364-9707
TEL: +86-752-205-1054	FAX: +86-752-205-1059
TEL: +86-592-238-5705	FAX: +86-592-239-8380
TEL: +86-756-3232-480	FAX: +86-756-3232-460
TEL: +852-2-740-6262	FAX: +852-2-375-8971
TEL: +886-2-2500-6956	FAX: +886-2-2503-2869
TEL: +886-7-237-0881	FAX: +886-7-238-7332
TEL: +65-6332-2322	FAX: +65-6332-5662
TEL: +63-2-807-6872	FAX: +63-2-809-1422
TEL: +66-2-254-4890	FAX: +66-2-256-6334
TEL: +60-3-7958-8355	FAX: +60-3-7958-8377
TEL: +60-4-2286453	FAX: +60-4-2286452
TEL: +81-75-365-1218	FAX: +81-75-365-1228
TEL: +81-45-476-2290	FAX: +81-45-476-2295